

Short circuit rugged 1200 V TRENCHSTOP™ IGBT 7 technology copacked with soft, fast recovery Emitter Controlled 7 diode

Features

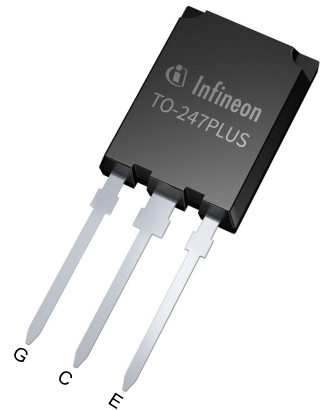
- $V_{CE} = 1200\text{ V}$
- $I_C = 100\text{ A}$
- IGBT co-packed with full current, soft and low Q_{rr} diode
- Low saturation voltage $V_{CEsat} = 2.0\text{ V}$ at $T_{vj} = 175^\circ\text{C}$
- Optimized for hard switching topologies (2-L inverter, 3-L NPC T-type, ...)
- Short circuit ruggedness $8\ \mu\text{s}$
- Wide range of dv/dt controllability
- Complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>

Potential applications

- Industrial drives
- Industrial power supplies
- Solar inverters

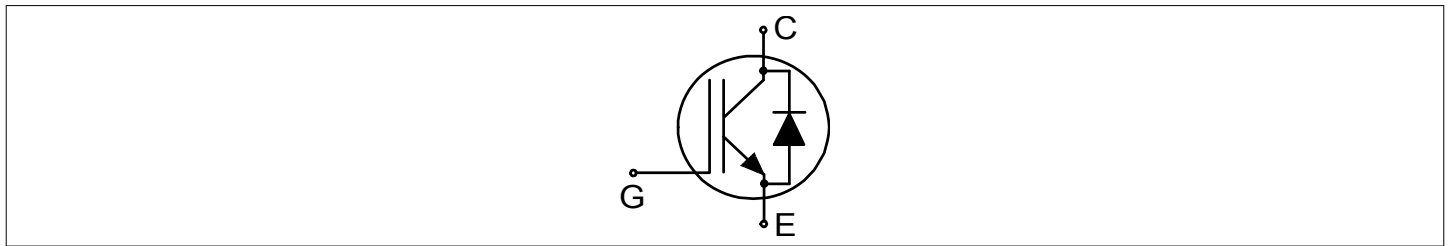
Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22



- Halogen-free
- Lead-free
- Green
- RoHS

Description



Type	Package	Marking
IKQ100N120CS7	PG-TO247-3-PLUS-NN3.7	K100MCS7

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1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	L_E			13		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W
IGBT thermal resistance, junction-case	$R_{th(j-c)}$			0.13	0.18	K/W
Diode thermal resistance, junction-case	$R_{th(j-c)}$			0.24	0.33	K/W

2 IGBT

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Collector-emitter voltage	V_{CE}	$T_{vj} \geq 25 \text{ °C}$	1200	V	
DC collector current, limited by T_{vjmax}	I_C	limited by bondwire	$T_c = 25 \text{ °C}$	188	A
			$T_c = 100 \text{ °C}$	126	
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpulse}		300	A	
Turn-off safe operating area		$V_{CE} \leq 1200 \text{ V}, T_{vj} \leq 175 \text{ °C}$	300	A	
Gate-emitter voltage	V_{GE}		± 20	V	
Transient gate-emitter voltage	V_{GE}	$t_p \leq 0.5 \text{ }\mu\text{s}, D < 0.001$	± 25	V	
Short-circuit withstand time	t_{SC}	$V_{CC} \leq 600 \text{ V}, V_{GE} = 15 \text{ V}$, Allowed number of short circuits < 1000, Time between short circuits $\geq 1.0 \text{ s}, T_{vj} = 150 \text{ °C}$	8	μs	
Power dissipation	P_{tot}	$T_{vj} \leq 175 \text{ °C}$	$T_c = 25 \text{ °C}$	824	W
			$T_c = 100 \text{ °C}$	412	

Table 3 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 100\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$	1.65	2	V
			$T_{vj} = 175\text{ °C}$		2	
Gate-emitter threshold voltage	V_{GEth}	$I_C = 2\text{ mA}, V_{CE} = V_{GE}$	5.1	5.7	6.5	V
Zero gate-voltage collector current	I_{CES}	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		40	μA
			$T_{vj} = 175\text{ °C}$		8700	
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$			100	nA
Transconductance	g_{fs}	$I_C = 100\text{ A}, V_{CE} = 20\text{ V}, T_{vj} = 175\text{ °C}$		36		S
Short-circuit collector current	I_{SC}	$V_{CC} \leq 600\text{ V}, V_{GE} = 15\text{ V}, t_{SC} \leq 8\text{ }\mu\text{s}$, Allowed number of short circuits < 1000, Time between short circuits $\geq 1.0\text{ s}$, $T_{vj} = 150\text{ °C}$		600		A
Input capacitance	C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 100\text{ kHz}$		14.5		nF
Output capacitance	C_{oes}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 100\text{ kHz}$		270		pF
Reverse transfer capacitance	C_{res}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 100\text{ kHz}$		60		pF
Gate charge	Q_G	$I_C = 100\text{ A}, V_{GE} = 15\text{ V}, V_{CC} = 960\text{ V}$		610		nC
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 1.6\text{ }\Omega, R_{G(off)} = 1.6\text{ }\Omega$	$T_{vj} = 25\text{ °C}, I_C = 100\text{ A}$	38		ns
			$T_{vj} = 175\text{ °C}, I_C = 100\text{ A}$		39	
Rise time (inductive load)	t_r	$V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 1.6\text{ }\Omega, R_{G(off)} = 1.6\text{ }\Omega$	$T_{vj} = 25\text{ °C}, I_C = 100\text{ A}$	26		ns
			$T_{vj} = 175\text{ °C}, I_C = 100\text{ A}$		29	
Turn-off delay time	$t_{d(off)}$	$V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 1.6\text{ }\Omega, R_{G(off)} = 1.6\text{ }\Omega$	$T_{vj} = 25\text{ °C}, I_C = 100\text{ A}$	200		ns
			$T_{vj} = 175\text{ °C}, I_C = 100\text{ A}$		270	
Fall time (inductive load)	t_f	$V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 1.6\text{ }\Omega, R_{G(off)} = 1.6\text{ }\Omega$	$T_{vj} = 25\text{ °C}, I_C = 100\text{ A}$	103		ns
			$T_{vj} = 175\text{ °C}, I_C = 100\text{ A}$		230	
Turn-on energy	E_{on}	$V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 1.6\text{ }\Omega, R_{G(off)} = 1.6\text{ }\Omega$	$T_{vj} = 25\text{ °C}, I_C = 100\text{ A}$	6.87		mJ
			$T_{vj} = 175\text{ °C}, I_C = 100\text{ A}$		10.1	

(table continues...)

Table 3 (continued) **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Turn-off energy	E_{off}	$V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 1.6\ \Omega,$ $R_{G(off)} = 1.6\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_C = 100\text{ A}$		4.71		mJ
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_C = 100\text{ A}$		8.84		
Total switching energy	E_{ts}	$V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 1.6\ \Omega,$ $R_{G(off)} = 1.6\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_C = 100\text{ A}$		11.6		mJ
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_C = 100\text{ A}$		18.9		
Operating junction temperature	T_{vj}		-40		175	$^\circ\text{C}$	

Note: Electrical Characteristic, at $T_{vj} = 25\text{ }^\circ\text{C}$, unless otherwise specified.

3 Diode

Table 4 **Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit	
Diode forward current, limited by T_{vjmax}	I_F	limited by bondwire	$T_c = 25\text{ }^\circ\text{C}$	155	A
			$T_c = 100\text{ }^\circ\text{C}$	101	
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpulse}		300	A	
Power dissipation	P_{tot}		$T_c = 25\text{ }^\circ\text{C}$	460	W
			$T_c = 100\text{ }^\circ\text{C}$	230	

Table 5 **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Diode forward voltage	V_F	$I_F = 100\text{ A}$	$T_{vj} = 25\text{ }^\circ\text{C}$		1.65	2.15	V
			$T_{vj} = 175\text{ }^\circ\text{C}$		1.6		
Diode reverse recovery time	t_{rr}	$V_R = 600\text{ V}, R_{G(on)} = 1.6\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_F = 100\text{ A}$		203		ns
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_F = 100\text{ A}$		351		
Diode reverse recovery charge	Q_{rr}	$V_R = 600\text{ V}, R_{G(on)} = 1.6\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_F = 100\text{ A}$		6.84		μC
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_F = 100\text{ A}$		15		

(table continues...)

Table 5 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Diode peak reverse recovery current	I_{rrm}	$V_R = 600\text{ V}, R_{G(on)} = 1.6\ \Omega$	$T_{vj} = 25\text{ °C}, I_F = 100\text{ A}$		62		A
			$T_{vj} = 175\text{ °C}, I_F = 100\text{ A}$		77		
Diode peak rate of fall of reverse recovery current	di_{rr}/dt	$V_R = 600\text{ V}, R_{G(on)} = 1.6\ \Omega$	$T_{vj} = 25\text{ °C}, I_F = 100\text{ A}$		-350		A/ μs
			$T_{vj} = 175\text{ °C}, I_F = 100\text{ A}$		-243		
Reverse recovery energy	E_{rec}	$V_R = 600\text{ V}, R_{G(on)} = 1.6\ \Omega$	$T_{vj} = 25\text{ °C}, I_F = 100\text{ A}$		2.12		mJ
			$T_{vj} = 175\text{ °C}, I_F = 100\text{ A}$		5.4		
Operating junction temperature	T_{vj}			-40		175	$^{\circ}\text{C}$

Note: For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

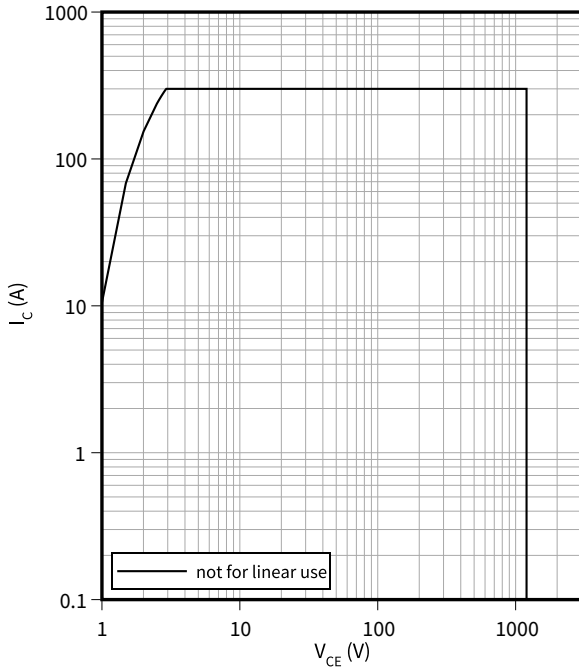
Dynamic test circuit, parasitic inductance $L_{\sigma} = 30\text{ nH}$, $C_{\sigma} = 18\text{ pF}$.

4 Characteristics diagrams

Reverse bias safe operating area

$$I_C = f(V_{CE})$$

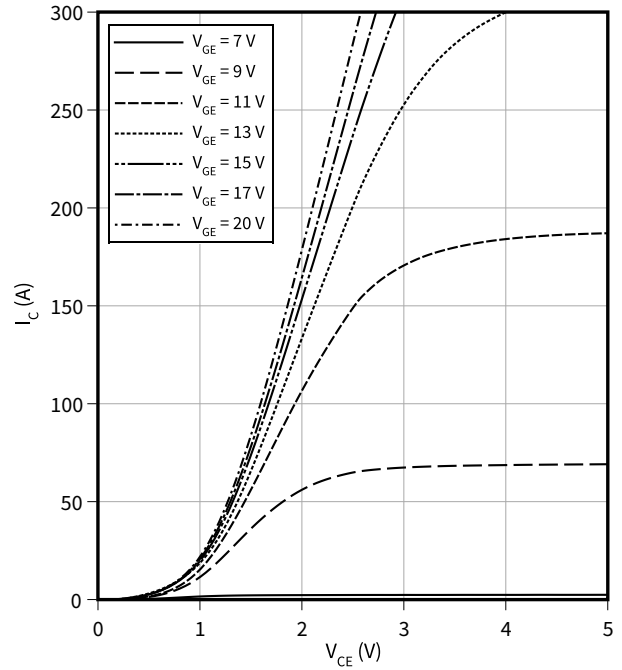
$$T_{vj} \leq 175\text{ °C}, V_{CE} = 25\text{ V}$$



Typical output characteristic

$$I_C = f(V_{CE})$$

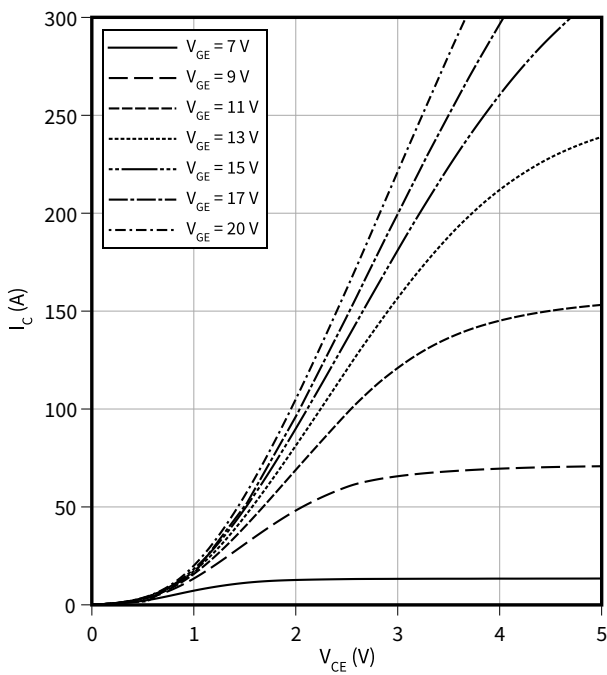
$$T_{vj} = 25\text{ °C}$$



Typical output characteristic

$$I_C = f(V_{CE})$$

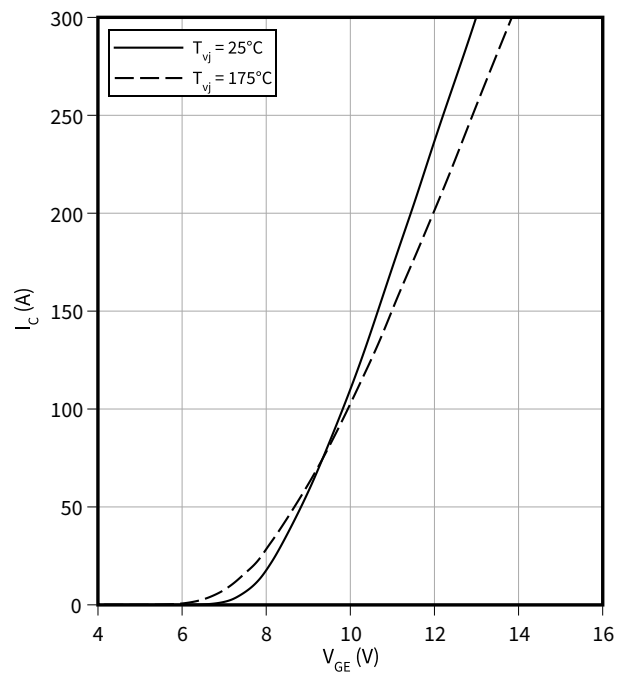
$$T_{vj} = 175\text{ °C}$$



Typical transfer characteristic

$$I_C = f(V_{GE})$$

$$V_{CE} = 20\text{ V}$$

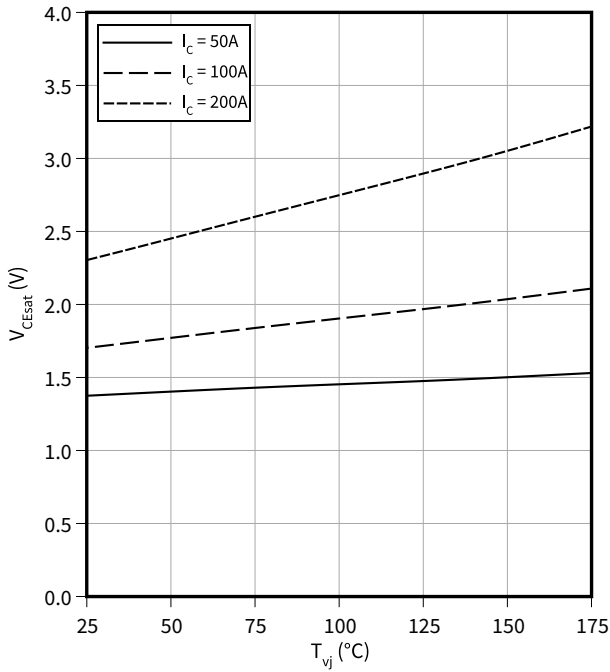


4 Characteristics diagrams

Typical collector-emitter saturation voltage as a function of junction temperature

$V_{CEsat} = f(T_{vj})$

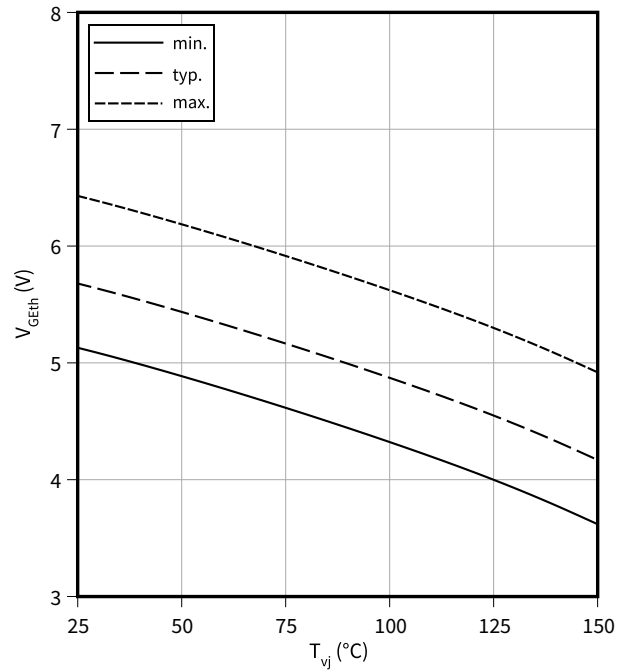
$V_{GE} = 15 \text{ V}$



Gate-emitter threshold voltage as a function of junction temperature

$V_{GEth} = f(T_{vj})$

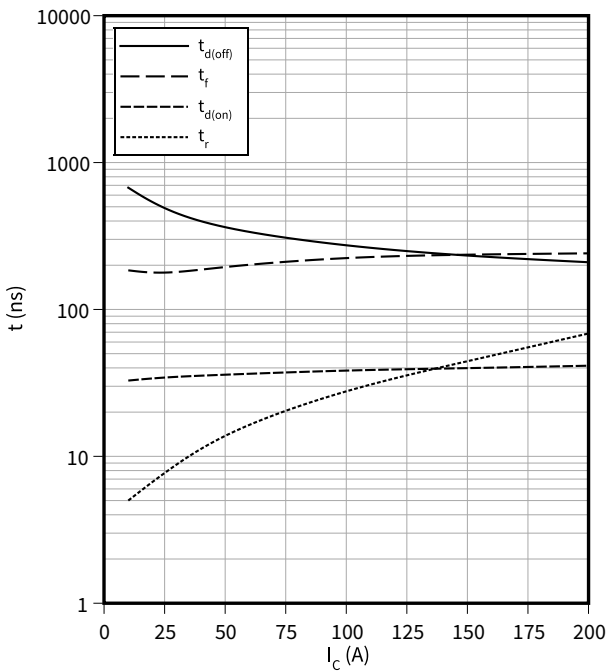
$I_c = 2 \text{ mA}$



Typical switching times as a function of collector current

$t = f(I_c)$

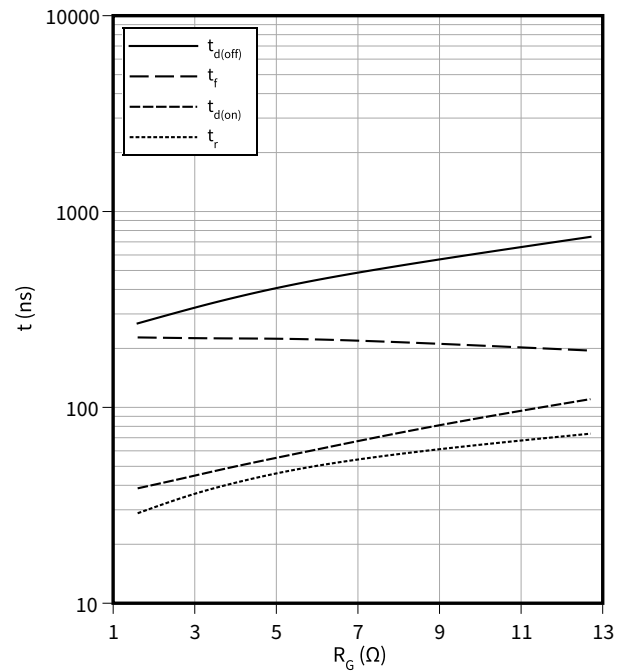
$V_{CC} = 600 \text{ V}, T_{vj} = 175 \text{ °C}, V_{GE} = 0/15 \text{ V}, R_G = 1.6 \text{ } \Omega$



Typical switching times as a function of gate resistor

$t = f(R_G)$

$I_c = 100 \text{ A}, V_{CC} = 600 \text{ V}, T_{vj} = 175 \text{ °C}, V_{GE} = 0/15 \text{ V}$

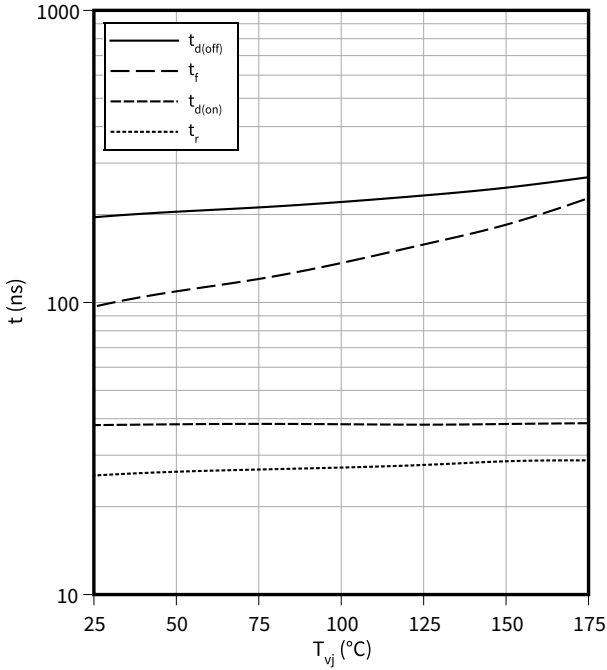


4 Characteristics diagrams

Typical switching times as a function of junction temperature

$t = f(T_{vj})$

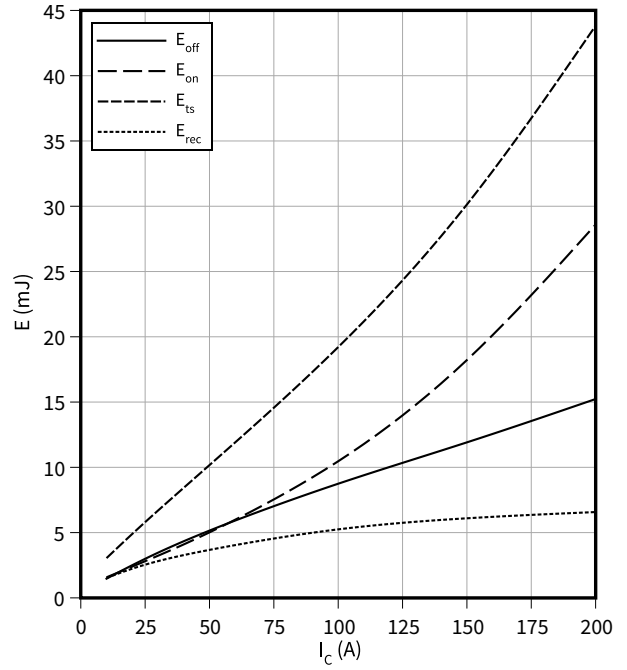
$I_C = 100\text{ A}, V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V}, R_G = 1.6\ \Omega$



Typical switching energy losses as a function of collector current

$E = f(I_C)$

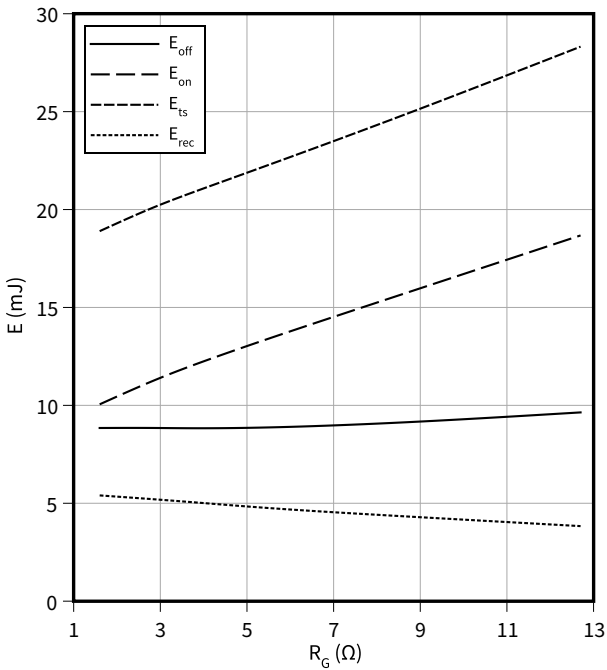
$V_{CC} = 600\text{ V}, T_{vj} = 175\text{ °C}, V_{GE} = 0/15\text{ V}, R_G = 1.6\ \Omega$



Typical switching energy losses as a function of gate resistor

$E = f(R_G)$

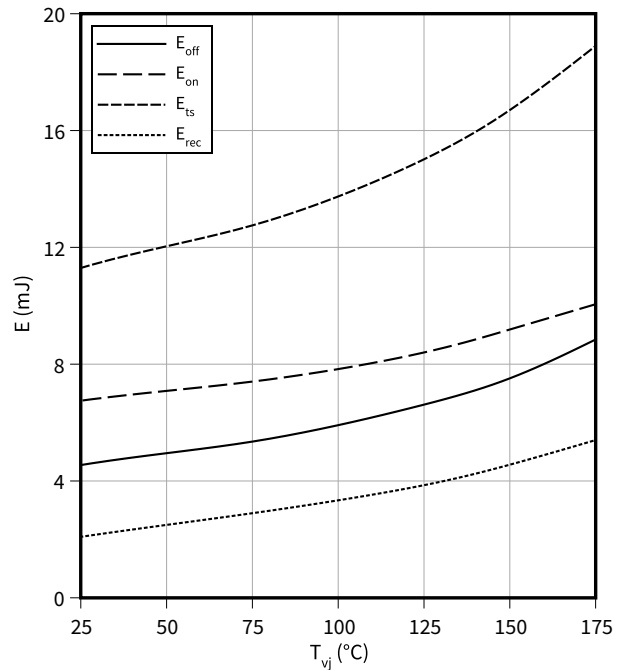
$I_C = 100\text{ A}, V_{CC} = 600\text{ V}, T_{vj} = 175\text{ °C}, V_{GE} = 0/15\text{ V}$



Typical switching energy losses as a function of junction temperature

$E = f(T_{vj})$

$I_C = 100\text{ A}, V_{CC} = 600\text{ V}, V_{GE} = 0/15\text{ V}, R_G = 1.6\ \Omega$

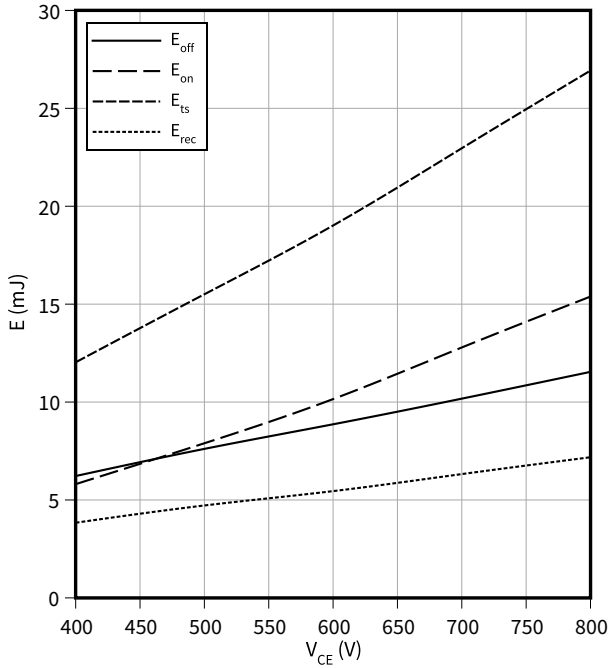


4 Characteristics diagrams

Typical switching energy losses as a function of collector emitter voltage

$E = f(V_{CE})$

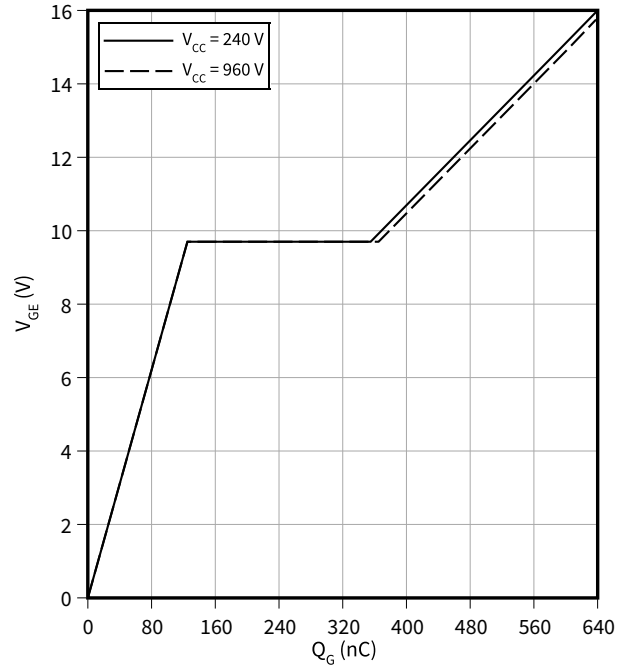
$I_C = 100\text{ A}$, $V_{GE} = 0/15\text{ V}$, $T_{vj} = 175\text{ °C}$, $R_G = 1.6\text{ }\Omega$



Typical gate charge

$V_{GE} = f(Q_G)$

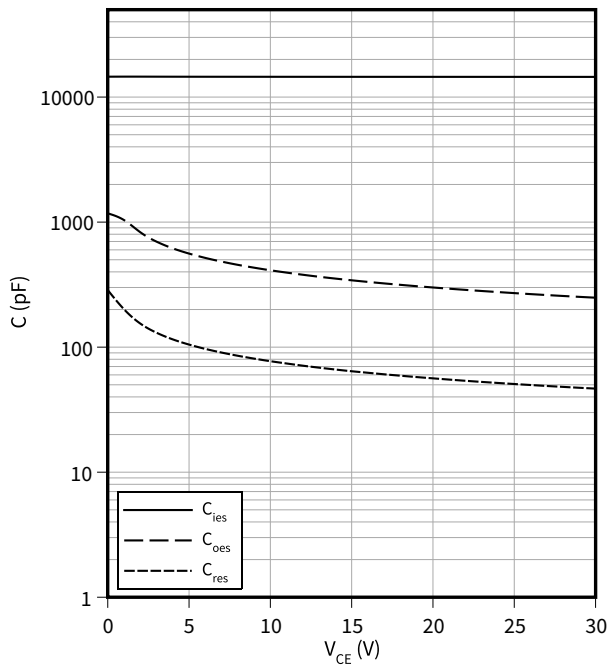
$I_C = 100\text{ A}$



Typical capacitance as a function of collector-emitter voltage

$C = f(V_{CE})$

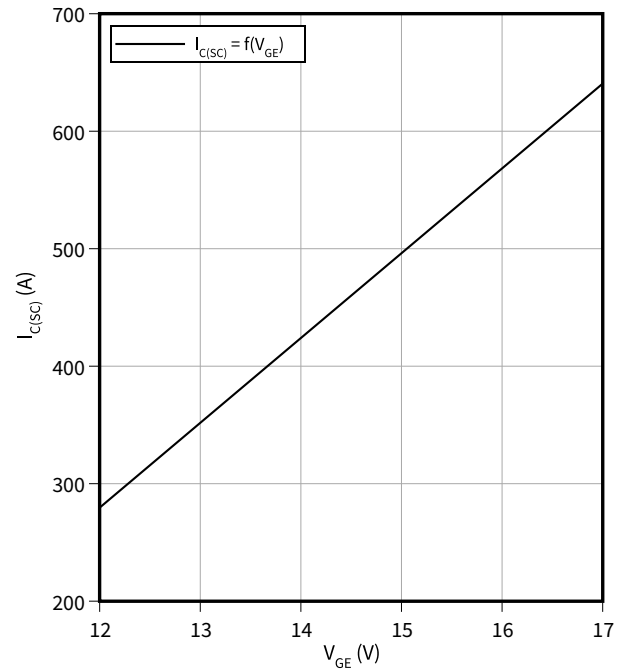
$f = 100\text{ kHz}$, $V_{GE} = 0\text{ V}$



Typical short circuit collector current as a function of gate-emitter voltage

$I_{C(SC)} = f(V_{GE})$

$T_{vj} = 150\text{ °C}$, $V_{CC} \leq 600\text{ V}$

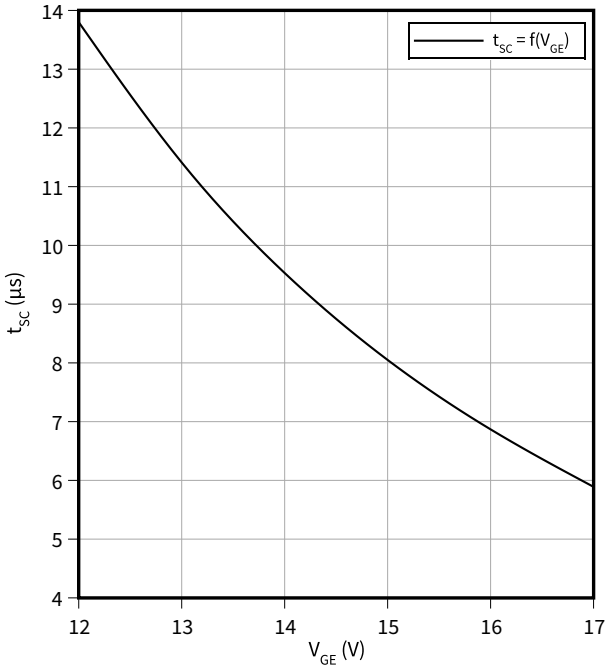


4 Characteristics diagrams

Short circuit withstand time as a function of gate-emitter voltage

$t_{SC} = f(V_{GE})$

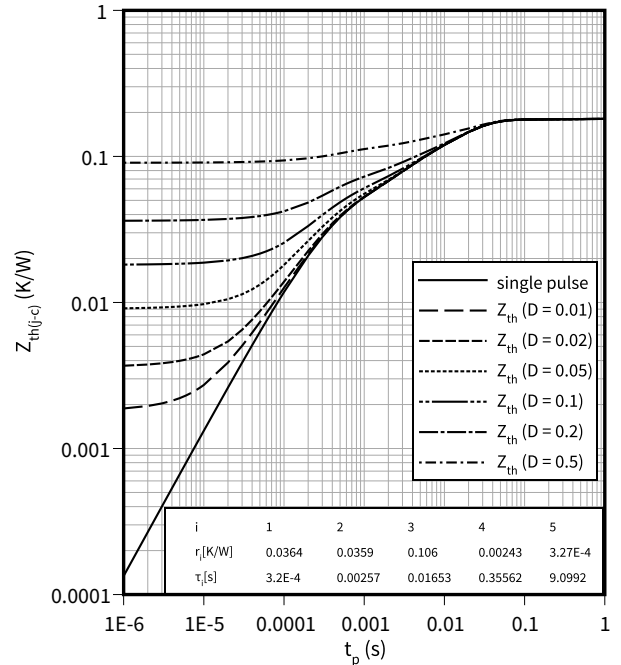
$T_{vj} \leq 150\text{ °C}, V_{CC} \leq 600\text{ V}$



IGBT transient thermal impedance as a function of pulse width

$Z_{th(j-c)} = f(t_p)$

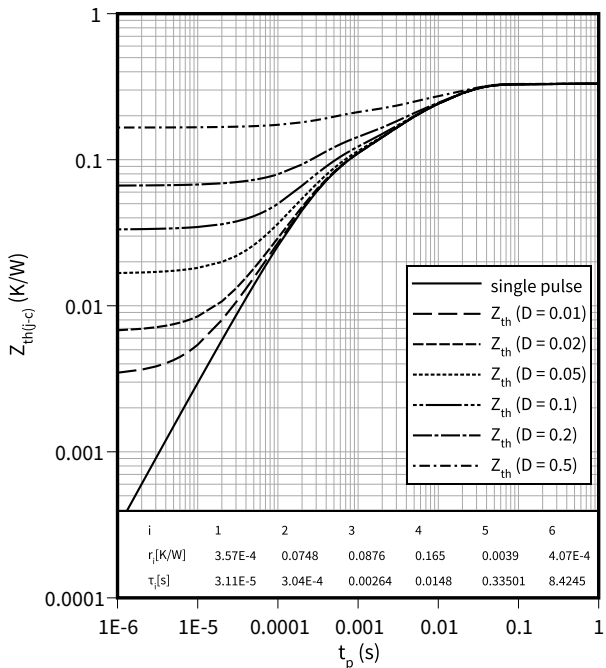
$D = t_p/T$



Diode transient thermal impedance as a function of pulse width

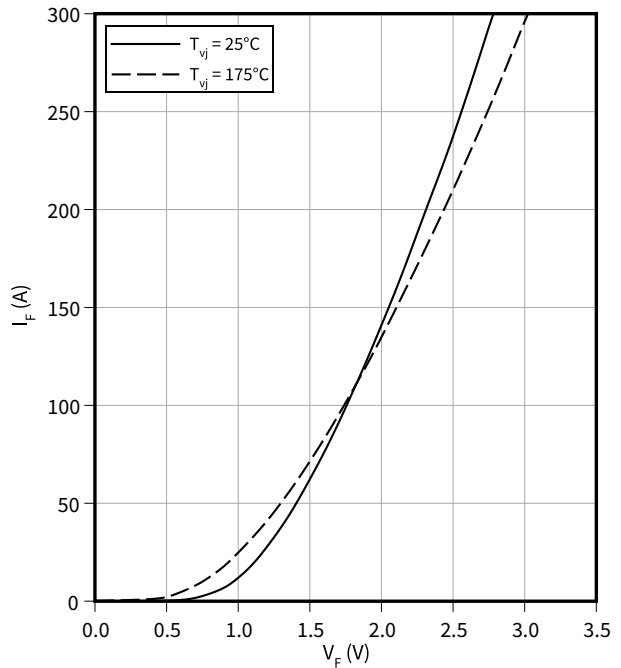
$Z_{th(j-c)} = f(t_p)$

$D = t_p/T$



Typical diode forward current as a function of forward voltage

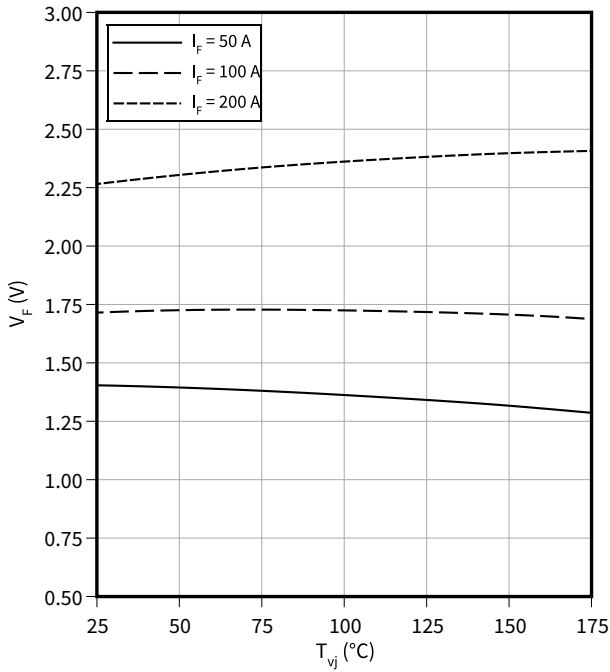
$I_F = f(V_F)$



4 Characteristics diagrams

Typical diode forward voltage as a function of junction temperature

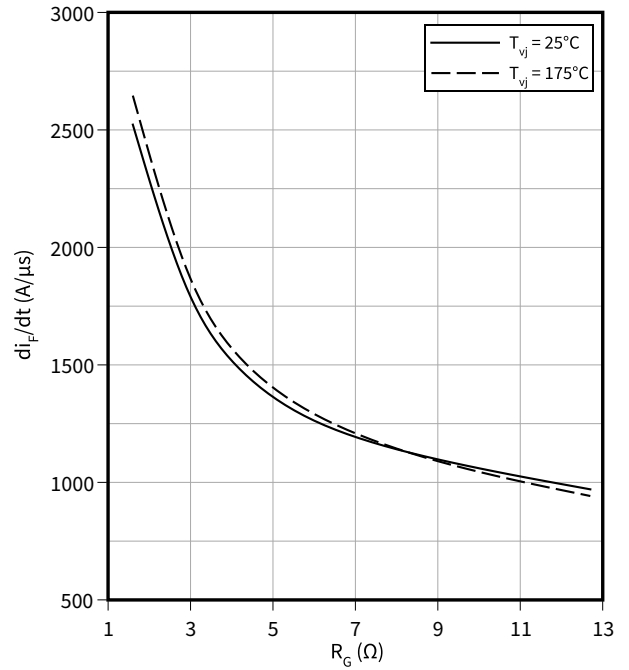
$V_F = f(T_{vj})$



Typical diode current slope as a function of gate resistor

$di_F/dt = f(R_G)$

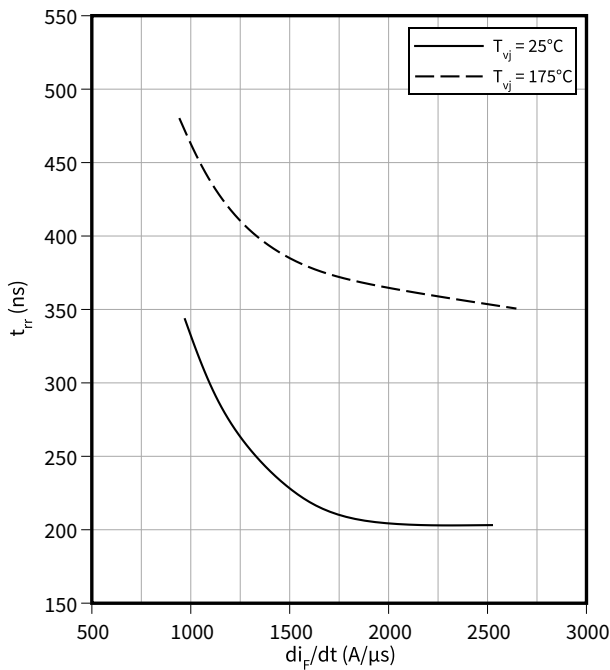
$V_R = 600$ V, $I_F = 100$ A



Typical reverse recovery time as a function of diode current slope

$t_{rr} = f(di_F/dt)$

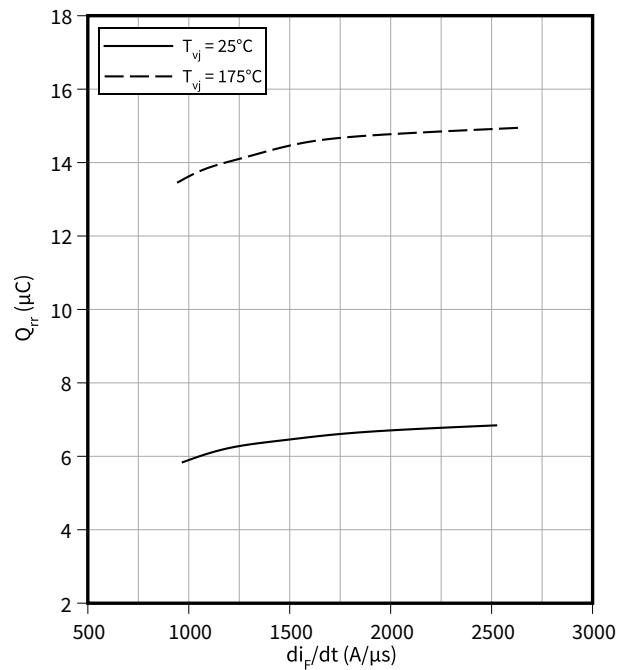
$V_R = 600$ V, $I_F = 100$ A



Typical reverse recovery charge as a function of diode current slope

$Q_{rr} = f(di_F/dt)$

$V_R = 600$ V, $I_F = 100$ A

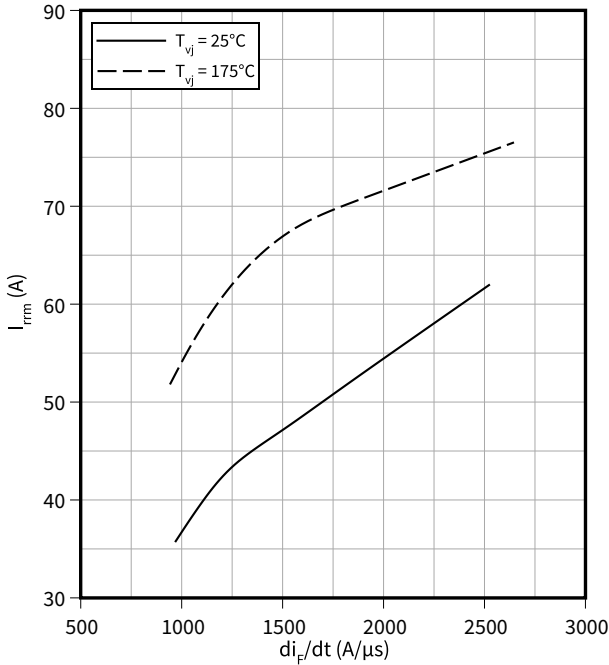


4 Characteristics diagrams

Typical reverse recovery current as a function of diode current slope

$$I_{rrm} = f(di_F/dt)$$

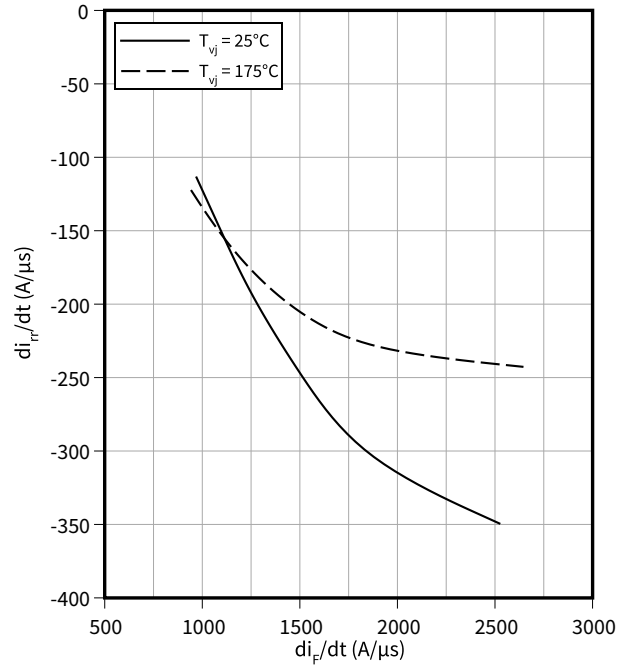
$V_R = 600\text{ V}, I_F = 100\text{ A}$



Typical diode peak rate of fall of reverse recovery current as a function of diode current slope

$$di_{rr}/dt = f(di_F/dt)$$

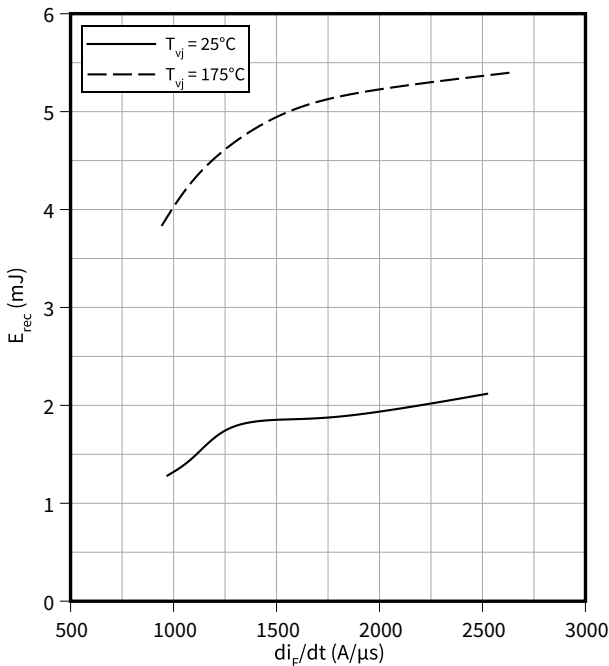
$V_R = 600\text{ V}, I_F = 100\text{ A}$



Typical reverse energy losses as a function of diode current slope

$$E_{rec} = f(di_F/dt)$$

$V_R = 600\text{ V}, I_F = 100\text{ A}$



5 Package outlines

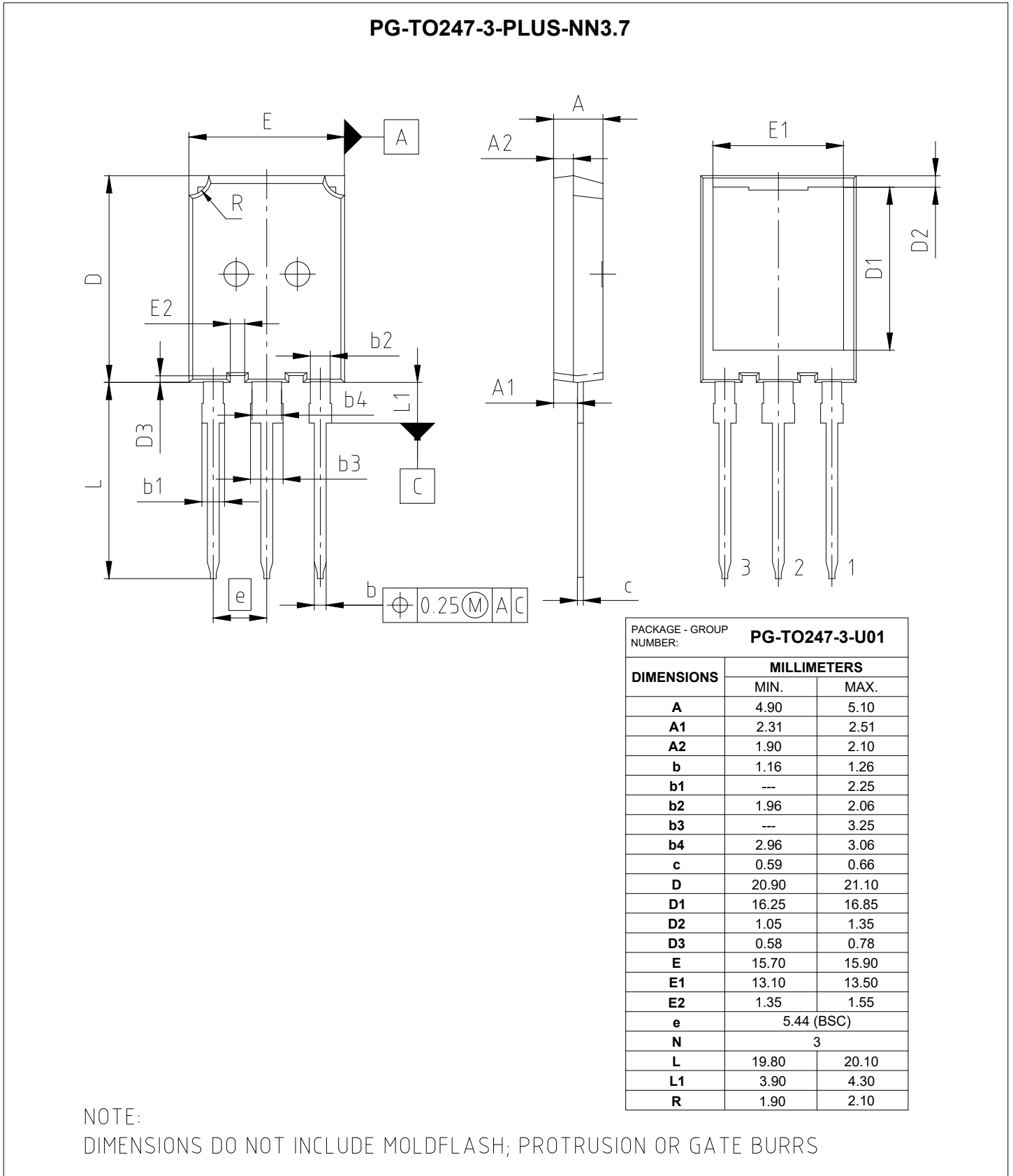


Figure 1

6 Testing conditions

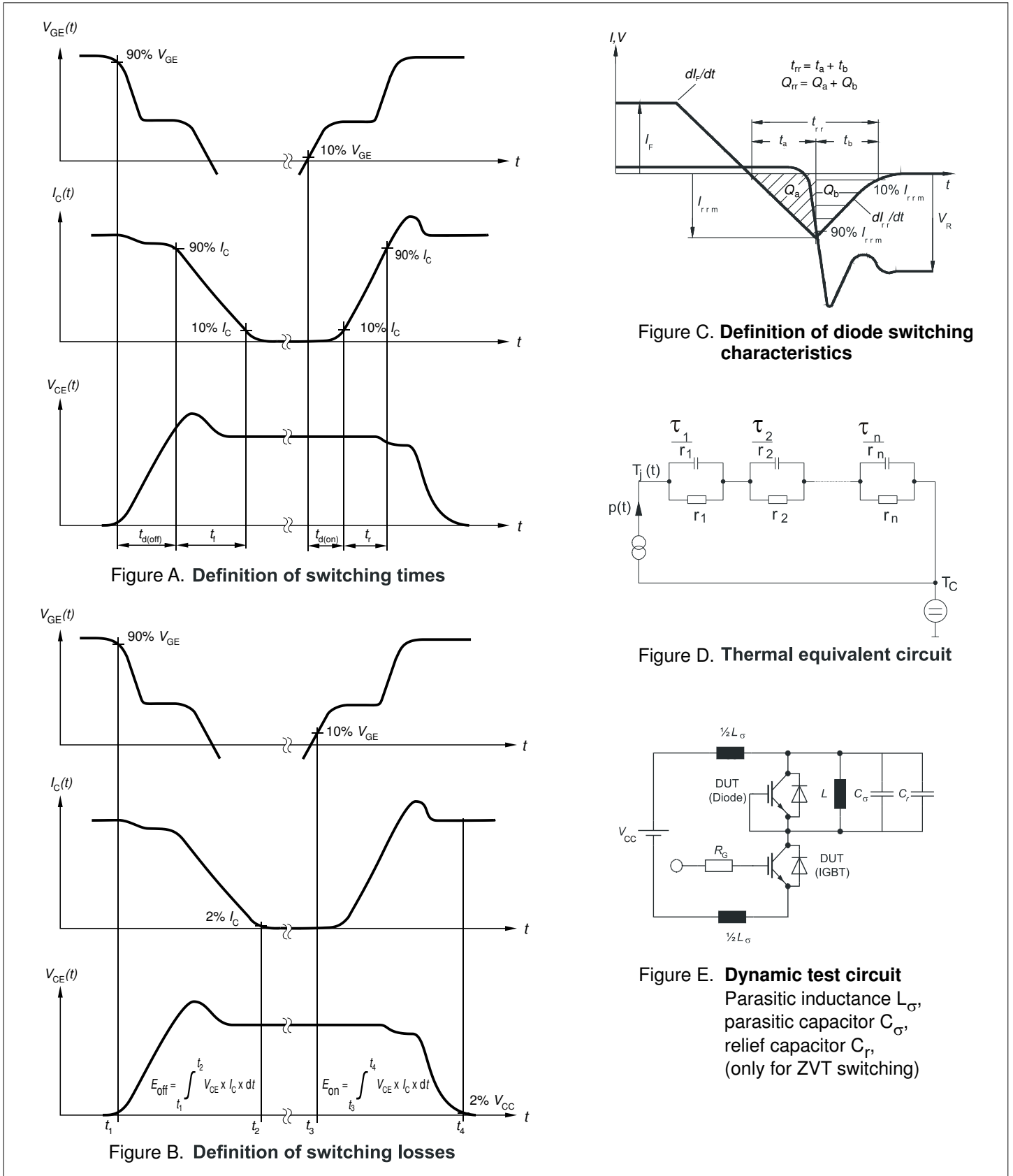


Figure 2

Revision history

Document revision	Date of release	Description of changes
0.10	2022-05-04	Target datasheet
1.00	2022-12-05	Final datasheet
1.10	2023-01-23	Correction of boundary condition of diagrams $I_{C(SC)} = f(V_{GE})$ and $t_{SC} = f(V_{GE})$ Change of product outline drawing on page 14

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